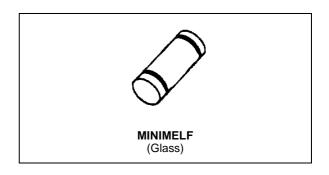


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown voltage, low turn-on voltage and ultrafast switching.

Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range.



ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	20	V
l _F	Forward Continuous Current	35	mA
P _{tot}	Power Dissipation	430	mW
T _{stg} Tj	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C
TL	Maximum Temperature for Soldering during 15	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-leads	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
V_{BR}	T _{amb} = 25°C	$I_R = 10\mu A$		20			V
V _F *	T _{amb} = 25°C	$I_F = 1mA$				0.41	V
	T _{amb} = 25°C	$I_F = 35mA$				1	
I _R *	T _{amb} = 25°C	V _R = 15V				0.1	μΑ

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 0V$	f = 1MHz			1.2	pF
τ	T _{amb} = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

^{*} Pulse test: $t_p \le 300 \mu s \ \delta < 2\%$.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

November 1994 1/4

Fig.1: Forward current versus forward voltage at different temperatures (typical values)

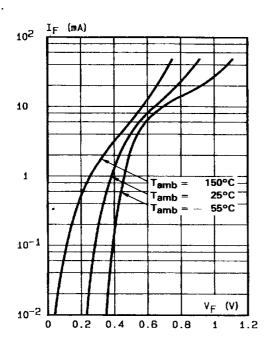


Fig.2 : Forward current versus forward voltage (typical values).

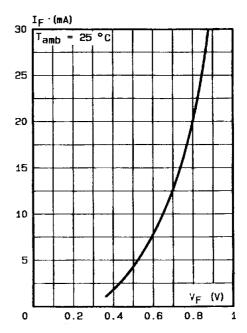


Fig.3: Reverse current versus ambient temperature.

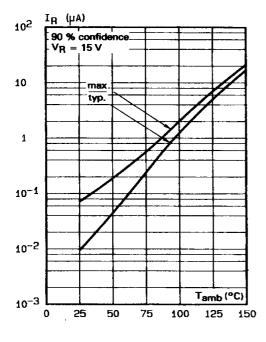
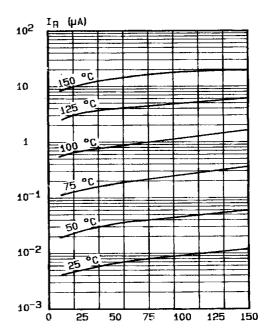


Fig.4: Reverse current versus continuous reverse voltage (typical values).



1.5 Tamb = 25°C

1.25 Tomb = 25°C

0.75 Tomb = 25°C

0.25 Tomb = 25°C

10

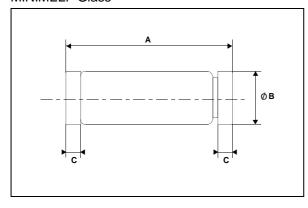
Fig.5: Capacitance C versus reverse applied voltage V_{p} (typical values).

PACKAGE MECHANICAL DATA

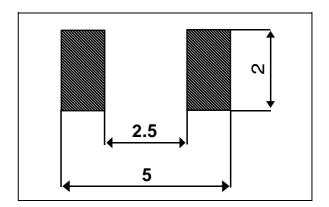
FOOT PRINT DIMENSIONS (Millimeter)

ν_R (ν)

MINIMELF Glass



0



	DIMENSIONS					
REF.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	3.3	3.6	0.130	0.142		
В	1.59	1.62	0.063	0.064		
С	0.4	0.5	0.016	0.020		

Marking: ring at cathode end. Weight: 0.05g

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